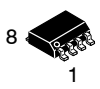
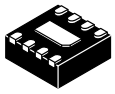
3.3 V 1:2 Fanout Differential LVPECL/LVDS to LVTTL Translator

MC100EPT26



SOIC−8 NB
D SUFFIX
CASE 751−07

TSSOP−8
DT SUFFIX
CASE 948R−02



DFN8
MN SUFFIX
CASE 506AA

Description

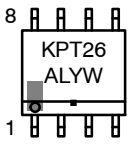
The MC100EPT26 is a 1:2 Fanout Differential LVPECL/LVDS to LVTTL translator. Because LVPECL (Positive ECL) or LVDS levels are used only +3.3 V and ground are required. The small outline 8−lead package and the 1:2 fanout design of the EPT26 makes it ideal for applications which require the low skew duplication of a signal in a tightly packed PC board.

The V_{BB} output allows the EPT26 to be used in a Single−Ended input mode. In this mode the V_{BB} output is tied to the $\overline{D0}$ input for a non−inverting buffer or the D0 input for an inverting buffer. If used, the V_{BB} pin should be bypassed to ground with > 0.01 μF capacitor. For a Single−Ended direct connection, use an external voltage reference source such as a resistor divider. Do not use V_{BB} for a Single−Ended direct connection or port to another device.

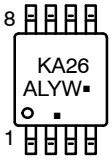
Features

- 1.4 ns Typical Propagation Delay
- Maximum Frequency = > 275 MHz Typical
- The 100 Series Contains Temperature Compensation
- Operating Range: V_{CC} = 3.0 V to 3.6 V with GND = 0 V
- 24 mA TTL outputs
- Q Outputs Will Default LOW with Inputs Open or at V_{EE}
- V_{BB} Output
- These Devices are Pb−Free, Halogen Free and are RoHS Compliant

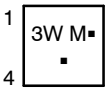
MARKING DIAGRAMS*



SOIC−8 NB



TSSOP−8



DFN8

A	= Assembly Location
L	= Wafer Lot
Y	= Year
W	= Work Week
M	= Date Code
▪	= Pb−Free Package

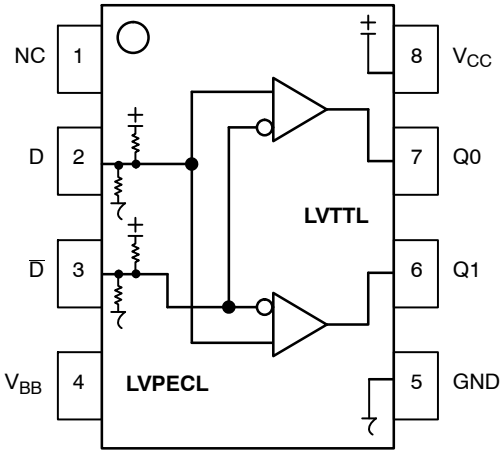
(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note AND8002/D.

ORDERING INFORMATION

Device	Package	Shipping†
MC100EPT26DG	SOIC−8 NB (Pb−Free)	98 Units/Tube
MC100EPT26DR2G	SOIC−8 NB (Pb−Free)	2500 Tape & Reel
MC100EPT26DTG	TSSOP−8 (Pb−Free)	100 Tape & Reel
MC100RPT26DTR2G	TSSOP−8 (Pb−Free)	2500 Tape & Reel
MC100EPT26MNR4G	DFN8 (Pb−Free)	1000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



(Top View)

Figure 1. 8−Lead Pinout and Logic Diagram

Table 1. PIN DESCRIPTION

Pin	Function
Q0, Q1	LVTTL Outputs
D0**, D1**	Differential LVPECL Inputs Pair
V_{CC}	Positive Supply
V_{BB}	Output Reference Voltage
GND	Ground
NC	No Connect
EP	(DFN8 only) Thermal exposed pad must be connected to a sufficient thermal conduit. Electrically connect to the most negative supply (GND) or leave unconnected, floating open.

** Pins will default to $V_{CC}/2$ when left open.

Table 2. ATTRIBUTES

Characteristics	Value
Internal Input Pulldown Resistor	50 kΩ
Internal Input Pullup Resistor	50 kΩ
ESD Protection Human Body Model Machine Model Charged Device Model	 > 1.5 kV > 100 V > 2 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb−Free Pkg
SOIC−8 NB TSSOP−8 DFN8	Level 1 Level 3 Level 1
Flammability Rating Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in
Transistor Count	117 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	

1. For additional information, see Application Note AND8003/D.

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V_{CC}	Positive Power Supply	GND = 0 V		3.8	V
V_{IN}	Input Voltage	GND = 0 V	$V_I \le V_{CC}$	0 to 3.8	V
I_{BB}	V_{BB} Sink/Source			±0.5	mA
T_A	Operating Temperature Range			−40 to +85	°C
T_{stg}	Storage Temperature Range			−65 to +150	°C
θ_{JA}	Thermal Resistance (Junction−to−Ambient)	0 lfpm 500 lfpm	SOIC−8 NB SOIC−8 NB	190 130	°C/W
θ_{JC}	Thermal Resistance (Junction−to−Case)	Standard Board	SOIC−8 NB	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction−to−Ambient)	0 lfpm 500 lfpm	TSSOP−8 TSSOP−8	185 140	°C/W
θ_{JC}	Thermal Resistance (Junction−to−Case)	Standard Board	TSSOP−8	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction−to−Ambient)	0 lfpm 500 lfpm	DFN8 DFN8	129 84	°C/W
T_{sol}	Wave Solder (Pb−Free)			265	°C
θ_{JC}	Thermal Resistance (Junction−to−Case)	(Note 2)	DFN8	35 to 40	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. JEDEC standard multilayer board − 2S2P (2 signal, 2 power)

Table 4. PECL INPUT DC CHARACTERISTICS (V_{CC} = 3.3 V; GND = 0.0 V (Note 3))

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
V_{IH}	Input HIGH Voltage (Single−Ended)	2075		2420	2075		2420	2075		2420	mV
V_{IL}	Input LOW Voltage (Single−Ended)	1355		1675	1355		1675	1355		1675	mV
V_{BB}	Output Voltage Reference	1775	1875	1975	1775	1875	1975	1775	1875	1975	V
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential) (Note 4)	1.2		3.3	1.2		3.3	1.2		3.3	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current D $\overline{D}$	 −150 −150			 −150 −150			 −150 −150			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

3. Input parameters vary 1:1 with V_{CC}.
4. V_{IHCMR} min varies 1:1 with GND, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 5. TTL OUTPUT DC CHARACTERISTICS (V_{CC} = 3.3 V; GND = 0.0 V; T_A = −40°C to 85°C)

Symbol	Characteristic	Condition	Min	Typ	Max	Unit
V_{OH}	Output HIGH Voltage	I_{OH} = −3.0 mA	2.4			V
V_{OL}	Output LOW Voltage	I_{OL} = 24 mA			0.5	V
I_{CCH}	Power Supply Current		10	25	35	mA
I_{CCL}	Power Supply Current		15	34	40	mA
I_{OS}	Output Short Circuit Current		−50		−150	mA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

Table 6. AC CHARACTERISTICS (V_{CC} = 3.0 V to 3.6 V; GND = 0.0 V (Note 5))

		−40°C			25°C			85°C			
Symbol	Characteristic	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Unit
f_{max}	Maximum Frequency (Figure 2)	275	350		275	350		275	350		MHz
t_{PLH}, t_{PHL}	Propagation Delay to Output Differential (Note 6)	1.2 1.2	1.5 1.5	2.0 1.8	1.2 1.2	1.5 1.5	2.0 1.8	1.3 1.2	1.7 1.5	2.2 1.8	ns
t_{SK++} t_{SK--} t_{SKPP}	Within Device Skew + + Within Device Skew − − Device−to−Device Skew (Note 7)		15 20 100	60 85 500		15 20 100	60 85 500		20 30 100	85 85 500	ps
t_{JITTER}	Random Clock Jitter (RMS) (Figure 2) @ ≤ 200 MHz @ > 200 MHz		6 20	30 275		6 40	30 275		6 170	30 275	ps
V_{PP}	Input Voltage Swing (Differential Configuration)	150	800	1200	150	800	1200	150	800	1200	mV
t_r t_f	Output Rise/Fall Times (0.8 V−2.0 V) Q, $\overline{Q}$	330	600	950	330	600	950	330	650	950	ps

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

5. Measured with a 750 mV 50% duty−cycle clock source. R_L = 500 Ω to GND and C_L = 20 pF to GND. Refer to Figure 3.
6. Reference (V_{CC} = 3.3 V ± 5%; GND = 0 V)
7. Skews are measured between outputs under identical transitions.

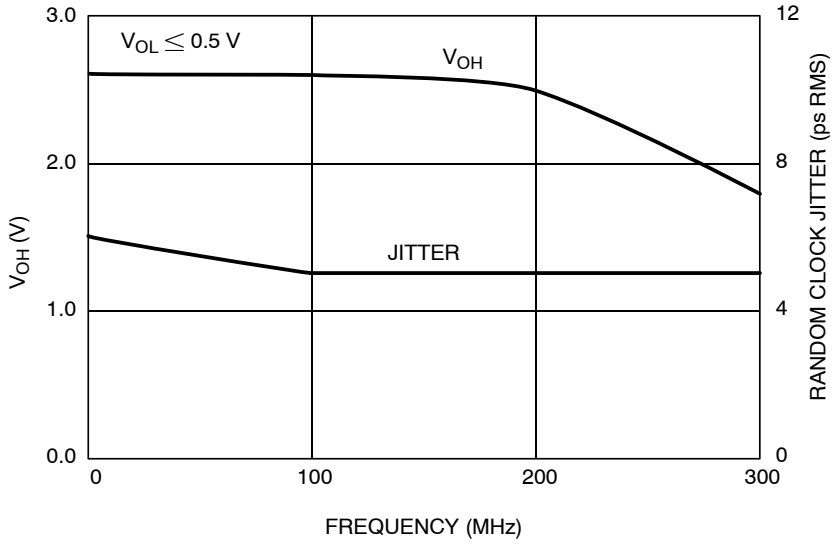


Figure 2. Typical V_{OH} / Jitter versus Frequency (25°C)

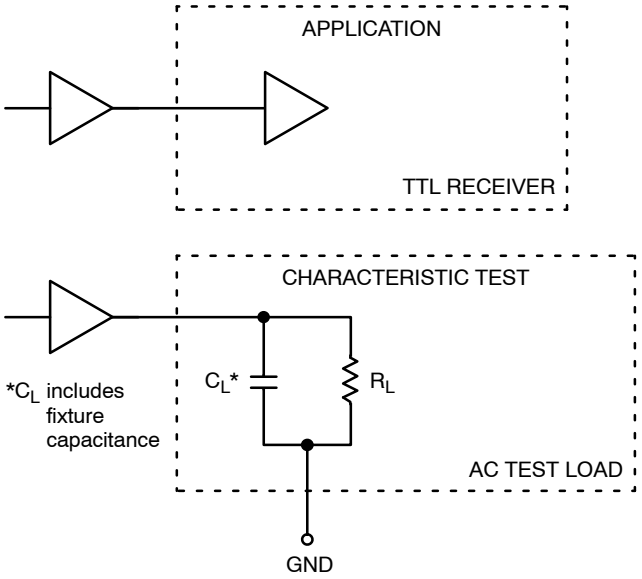
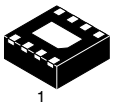


Figure 3. TTL Output Loading Used for Device Evaluation

Resource Reference of Application Notes

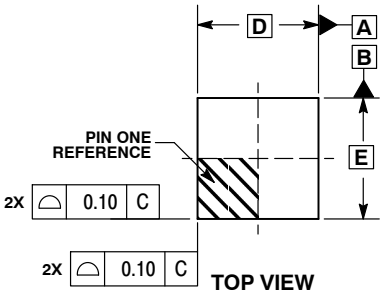
AN1405/D – ECL Clock Distribution Techniques
AN1406/D – Designing with PECL (ECL at +5.0 V)
AN1503/D – ECLinPS™ I/O SPiCE Modeling Kit
AN1504/D – Metastability and the ECLinPS Family
AN1568/D – Interfacing Between LVDS and ECL
AN1672/D – The ECL Translator Guide
AND8001/D – Odd Number Counters Design
AND8002/D – Marking and Date Codes
AND8020/D – Termination of ECL Logic Devices
AND8066/D – Interfacing with ECLinPS
AND8090/D – AC Characteristics of ECL Devices

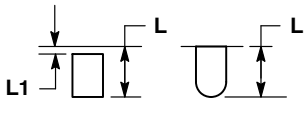


SCALE 4:1

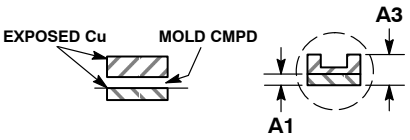
DFN8 2x2, 0.5P
CASE 506AA
ISSUE F

DATE 04 MAY 2016





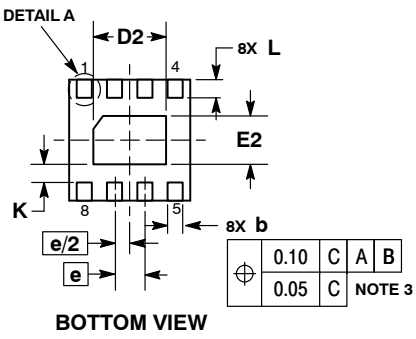
DETAIL A
OPTIONAL CONSTRUCTIONS



DETAIL B
ALTERNATE CONSTRUCTIONS

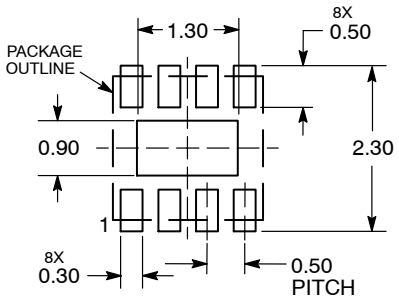
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994 .
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS	
DIM	MIN	MAX
A	0.80	1.00
A1	0.00	0.05
A3	0.20 REF	
b	0.20	0.30
D	2.00 BSC	
D2	1.10	1.30
E	2.00 BSC	
E2	0.70	0.90
e	0.50 BSC	
K	0.30 REF	
L	0.25	0.35
L1	---	0.10



BOTTOM VIEW

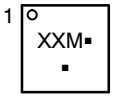
RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code
▪ = Pb−Free Device

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

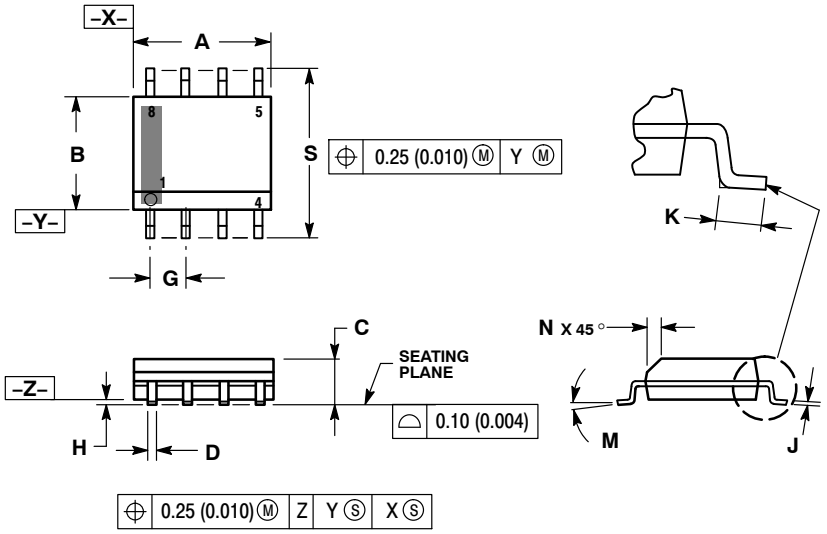
DOCUMENT NUMBER:	**98AON18658D**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	**DFN8, 2.0X2.0, 0.5MM PITCH**		**PAGE 1 OF 1**

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

SCALE 1:1

SOIC−8 NB
CASE 751−07
ISSUE AK

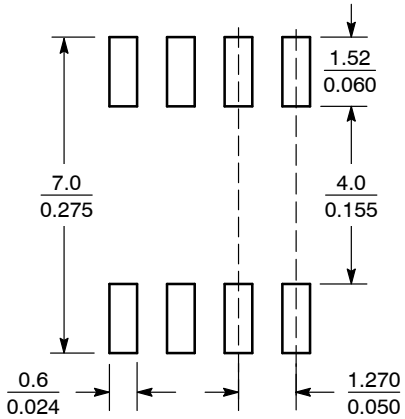
DATE 16 FEB 2011



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751−01 THRU 751−06 ARE OBSOLETE. NEW STANDARD IS 751−07.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

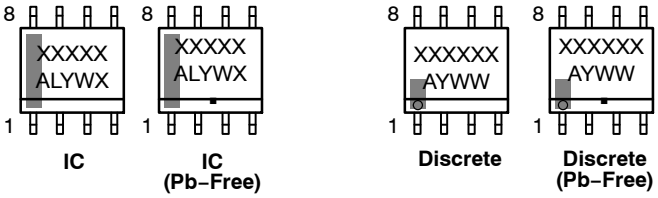
SOLDERING FOOTPRINT*



SCALE 6:1 (mm / inches)

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



IC | IC (Pb−Free) | Discrete | Discrete (Pb−Free)

XXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	**98ASB42564B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**SOIC−8 NB**	**PAGE 1 OF 2**

SOIC−8 NB
CASE 751−07
ISSUE AK

DATE 16 FEB 2011

STYLE 1:
PIN 1. EMITTER
2. COLLECTOR
3. COLLECTOR
4. EMITTER
5. EMITTER
6. BASE
7. BASE
8. EMITTER

STYLE 2:
PIN 1. COLLECTOR, DIE, #1
2. COLLECTOR, #1
3. COLLECTOR, #2
4. COLLECTOR, #2
5. BASE, #2
6. EMITTER, #2
7. BASE, #1
8. EMITTER, #1

STYLE 3:
PIN 1. DRAIN, DIE #1
2. DRAIN, #1
3. DRAIN, #2
4. DRAIN, #2
5. GATE, #2
6. SOURCE, #2
7. GATE, #1
8. SOURCE, #1

STYLE 4:
PIN 1. ANODE
2. ANODE
3. ANODE
4. ANODE
5. ANODE
6. ANODE
7. ANODE
8. COMMON CATHODE

STYLE 5:
PIN 1. DRAIN
2. DRAIN
3. DRAIN
4. DRAIN
5. GATE
6. GATE
7. SOURCE
8. SOURCE

STYLE 6:
PIN 1. SOURCE
2. DRAIN
3. DRAIN
4. SOURCE
5. SOURCE
6. GATE
7. GATE
8. SOURCE

STYLE 7:
PIN 1. INPUT
2. EXTERNAL BYPASS
3. THIRD STAGE SOURCE
4. GROUND
5. DRAIN
6. GATE 3
7. SECOND STAGE Vd
8. FIRST STAGE Vd

STYLE 8:
PIN 1. COLLECTOR, DIE #1
2. BASE, #1
3. BASE, #2
4. COLLECTOR, #2
5. COLLECTOR, #2
6. EMITTER, #2
7. EMITTER, #1
8. COLLECTOR, #1

STYLE 9:
PIN 1. EMITTER, COMMON
2. COLLECTOR, DIE #1
3. COLLECTOR, DIE #2
4. EMITTER, COMMON
5. EMITTER, COMMON
6. BASE, DIE #2
7. BASE, DIE #1
8. EMITTER, COMMON

STYLE 10:
PIN 1. GROUND
2. BIAS 1
3. OUTPUT
4. GROUND
5. GROUND
6. BIAS 2
7. INPUT
8. GROUND

STYLE 11:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

STYLE 12:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 13:
PIN 1. N.C.
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 14:
PIN 1. N−SOURCE
2. N−GATE
3. P−SOURCE
4. P−GATE
5. P−DRAIN
6. P−DRAIN
7. N−DRAIN
8. N−DRAIN

STYLE 15:
PIN 1. ANODE 1
2. ANODE 1
3. ANODE 1
4. ANODE 1
5. CATHODE, COMMON
6. CATHODE, COMMON
7. CATHODE, COMMON
8. CATHODE, COMMON

STYLE 16:
PIN 1. EMITTER, DIE #1
2. BASE, DIE #1
3. EMITTER, DIE #2
4. BASE, DIE #2
5. COLLECTOR, DIE #2
6. COLLECTOR, DIE #2
7. COLLECTOR, DIE #1
8. COLLECTOR, DIE #1

STYLE 17:
PIN 1. VCC
2. V2OUT
3. V1OUT
4. TXE
5. RXE
6. VEE
7. GND
8. ACC

STYLE 18:
PIN 1. ANODE
2. ANODE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. CATHODE
8. CATHODE

STYLE 19:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. MIRROR 2
7. DRAIN 1
8. MIRROR 1

STYLE 20:
PIN 1. SOURCE (N)
2. GATE (N)
3. SOURCE (P)
4. GATE (P)
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 21:
PIN 1. CATHODE 1
2. CATHODE 2
3. CATHODE 3
4. CATHODE 4
5. CATHODE 5
6. COMMON ANODE
7. COMMON ANODE
8. CATHODE 6

STYLE 22:
PIN 1. I/O LINE 1
2. COMMON CATHODE/VCC
3. COMMON CATHODE/VCC
4. I/O LINE 3
5. COMMON ANODE/GND
6. I/O LINE 4
7. I/O LINE 5
8. COMMON ANODE/GND

STYLE 23:
PIN 1. LINE 1 IN
2. COMMON ANODE/GND
3. COMMON ANODE/GND
4. LINE 2 IN
5. LINE 2 OUT
6. COMMON ANODE/GND
7. COMMON ANODE/GND
8. LINE 1 OUT

STYLE 24:
PIN 1. BASE
2. EMITTER
3. COLLECTOR/ANODE
4. COLLECTOR/ANODE
5. CATHODE
6. CATHODE
7. COLLECTOR/ANODE
8. COLLECTOR/ANODE

STYLE 25:
PIN 1. VIN
2. N/C
3. REXT
4. GND
5. IOUT
6. IOUT
7. IOUT
8. IOUT

STYLE 26:
PIN 1. GND
2. dv/dt
3. ENABLE
4. ILIMIT
5. SOURCE
6. SOURCE
7. SOURCE
8. VCC

STYLE 27:
PIN 1. ILIMIT
2. OVLO
3. UVLO
4. INPUT+
5. SOURCE
6. SOURCE
7. SOURCE
8. DRAIN

STYLE 28:
PIN 1. SW_TO_GND
2. DASIC_OFF
3. DASIC_SW_DET
4. GND
5. V_MON
6. VBULK
7. VBULK
8. VIN

STYLE 29:
PIN 1. BASE, DIE #1
2. EMITTER, #1
3. BASE, #2
4. EMITTER, #2
5. COLLECTOR, #2
6. COLLECTOR, #2
7. COLLECTOR, #1
8. COLLECTOR, #1

STYLE 30:
PIN 1. DRAIN 1
2. DRAIN 1
3. GATE 2
4. SOURCE 2
5. SOURCE 1/DRAIN 2
6. SOURCE 1/DRAIN 2
7. SOURCE 1/DRAIN 2
8. GATE 1

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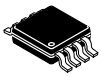
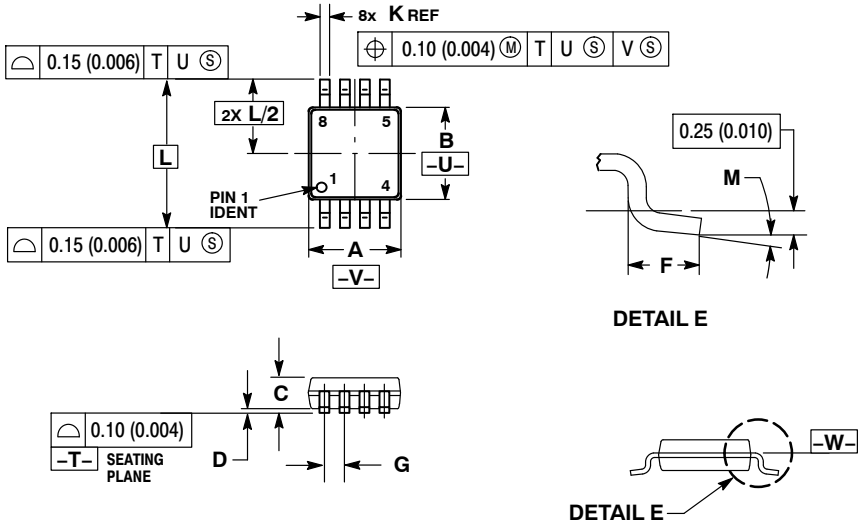
DESCRIPTION:	**SOIC−8 NB**		**PAGE 2 OF 2**

TSSOP 8
CASE 948R–02
ISSUE A

DATE 04/07/2000



SCALE 2:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	2.90	3.10	0.114	0.122
B	2.90	3.10	0.114	0.122
C	0.80	1.10	0.031	0.043
D	0.05	0.15	0.002	0.006
F	0.40	0.70	0.016	0.028
G	0.65 BSC		0.026 BSC	
K	0.25	0.40	0.010	0.016
L	4.90 BSC		0.193 BSC	
M	0°	6°	0°	6°

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